



09/855,532.

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PTO/SB/17 (07-06)  
Approved for use through 01/31/2007. OMB 0651-0032  
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Under the Paperwork Reduction Act of 1995, no person is required to respond to a collection of information unless it displays a valid OMB control number.

<b>Effective on 12/08/2004.</b> <b>Fees pursuant to the Consolidated Appropriations Act, 2005 (H.R. 4818).</b> <b>FEE TRANSMITTAL</b> <b>For FY 2006</b>		<b>Complete if Known</b>	
<input type="checkbox"/> Applicant claims small entity status. See 37 CFR 1.27		Application Number	Patent#: 7,142,577
<b>TOTAL AMOUNT OF PAYMENT</b> (\$) 100.00		Filing Date	Issued: November 28, 2006
		First Named Inventor	Joseph E. Geusic
		Examiner Name	A. Rodriguez
		Art Unit	2828
		Attorney Docket No.	M4065.0439/P439

<b>METHOD OF PAYMENT</b> (check all that apply)	
<input type="checkbox"/> Check	<input checked="" type="checkbox"/> Credit Card
<input type="checkbox"/> Money Order	<input type="checkbox"/> None
<input type="checkbox"/> Other (please identify): _____	
<input checked="" type="checkbox"/> Deposit Account    Deposit Account Number: <u>04-1073</u> Deposit Account Name: <u>Dickstein Shapiro LLP</u>	
For the above-identified deposit account, the Director is hereby authorized to: (check all that apply)	
<input type="checkbox"/> Charge fee(s) indicated below	<input type="checkbox"/> Charge fee(s) indicated below, except for the filing fee
<input checked="" type="checkbox"/> Charge any additional fee(s) or underpayments of fee(s) under 37 CFR 1.16 and 1.17	<input checked="" type="checkbox"/> Credit any overpayments

<b>FEE CALCULATION</b>								
<b>1. BASIC FILING, SEARCH, AND EXAMINATION FEES</b>								
	<b>FILING FEES</b>		<b>SEARCH FEES</b>		<b>EXAMINATION FEES</b>			
		<b>Small Entity</b>		<b>Small Entity</b>		<b>Small Entity</b>		
<b>Application Type</b>	<b>Fee (\$)</b>	<b>Fee (\$)</b>	<b>Fee (\$)</b>	<b>Fee (\$)</b>	<b>Fee (\$)</b>	<b>Fee (\$)</b>	<b>Fees Paid (\$)</b>	
Utility	300	150	500	250	200	100		
Design	200	100	100	50	130	65		
Plant	200	100	300	150	160	80		
Reissue	300	150	500	250	600	300		
Provisional	200	100	0	0	0	0		
<b>2. EXCESS CLAIM FEES</b>								
							<b>Small Entity</b>	
<b>Fee Description</b>							<b>Fee (\$)</b>	
Each claim over 20 (including Reissues)							50	
Each independent claim over 3 (including Reissues)							200	
Multiple dependent claims							360	
<b>Total Claims</b> <b>Extra Claims</b> <b>Fee (\$)</b> <b>Fee Paid (\$)</b>							<b>Multiple Dependent Claims</b>	
_____ - = _____ x _____ = _____							<b>Fee (\$)</b> <b>Fee Paid (\$)</b>	
HP = highest number of total claims paid for, if greater than 20.								
<b>Indep. Claims</b> <b>Extra Claims</b> <b>Fee (\$)</b> <b>Fee Paid (\$)</b>								
_____ - = _____ x _____ = _____								
HP = highest number of independent claims paid for, if greater than 3.								
<b>3. APPLICATION SIZE FEE</b>								
If the specification and drawings exceed 100 sheets of paper (excluding electronically filed sequence or computer listings under 37 CFR 1.52(e)), the application size fee due is \$250 (\$125 for small entity) for each additional 50 sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s).								
<b>Total Sheets</b>		<b>Extra Sheets</b>	<b>Number of each additional 50 or fraction thereof</b>		<b>Fee (\$)</b>	<b>Fee Paid (\$)</b>		
_____ - 100 = _____		/50	_____ (round up to a whole number) x _____		= _____			
<b>4. OTHER FEE(S)</b>								
Non-English Specification, \$130 fee (no small entity discount)								
Other (e.g., late filing surcharge): 1811 Certificate of correction							100.00	

<b>SUBMITTED BY</b>			
Signature	<u>Thomas J. D'Amico</u>	Registration No. (Attorney/Agent)	28,371
Name (Print/Type)	Thomas J. D'Amico	Telephone	(202) 420-2232
		Date	January 10, 2007

**Certificate**  
**JAN 12 2007**  
**of Correction**

**JAN 16 2007**



Docket No.: M4065.0439/P439  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:  
Joseph E. Geusic et al.

Patent No.: 7,142,577

Issued: November 28, 2006

For: METHOD OF FORMING MIRRORS BY  
SURFACE TRANSFORMATION OF EMPTY  
SPACES IN SOLID STATE MATERIALS  
AND STRUCTURES THEREON (AS  
AMENDED)

**REQUEST FOR CERTIFICATE OF CORRECTION  
PURSUANT TO 37 CFR 1.322 & 1.323**

Attention: Certificate of Correction Branch  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentees noted errors which should be corrected.

In the "Other Publications" portion of References Cited, the PTO omitted the following publication which should be added:

Yang, Peldong; Rizvi, A.H.; Messer, B.; Chmelka, B.F.; Whitesides, G.M.; Stucky, G.D., Patterning Porous Oxides within Microchannel Networks, Adv. Mater., 13(6) Mar 16, 2001, 427-431.

01/11/2007 MAHMED2 00000175 7142577

01 FC:1811

100.00 0P

DSMDB-2195778v01

JAN 16 2007

Also, in "Other Publications," the PTO made the following errors to be corrected:

"Asoli, Hidetaka; Nishio, K.; Nakao, M.; Yokoo, A.; Tamaura, T.; Masuda, H., Fabrication of ideally ordered anodic porous alumina with 63 nm hole periodicity using sulfuric acid, J. Vac."

Should read

--Asoli, Hidetaka; Nishio, K.; Nakao, M.; Yokoo, A.; Tamaura, T.; Masuda, H., Fabrication of ideally ordered anodic porous alumina with 63 nm hole periodicity using sulfuric acid, J. Vac. Sci. Technol. B 19(2) Mar/April (2001) 569-572.--;

"Beauvais, Jacques; Lavallee, E.; Drouin, D.; Turcotte, D., Nano-Imprint Lithography Using Materials Fabricated by Sidwell Process, J. Vac. Sci. Technol. B, 17, 2957 (1999)."

Should read

--Beauvais, Jacques; Lavallee, E.; Drouin, D.; Turcotte, D., Nano-Imprint Lithography Using Materials Fabricated by Sidwell Process, J. Vac. Sci. Technol. B, 17, 2957 (1999).--;

"Berti, M.; Mazzi, G.; Calagnile, L.; Drigo, A.V.; Merli, P.G.; Migliori, A., Composition and structure of Si-Ge layers produced by ion implantation and laser melting, J. Mater. Res., 6(10) Oct. 1991, 2120-2126."

Should read

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"Xuan, Peiqi; Keczierski, J.; Subranmanian, V.; Bokor, J.; King, T.-J.; Hu, C., 60nm Planarized Ultra-thin Body Solid Phase Epitaxy MOSFETs, IEEE 58th DRC Meeting, Conf. Digest, Jun. 19-21, 2001, 67-68."

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JAN 16 2007

In the Specification, Patentees made the following errors to be corrected:

Column 8, line 24, "the to surface" should read --the surface--;

Column 8, line 58, "extend" should read --extent--; and

Column 9, line 11, "and been spaced" should read --and being spaced--.

In Claim 52, Applicant made the following error to be corrected:

Column 12, line 10, "being is" should read --being--.

Some of the errors were found in the application as filed by Applicants.

Please charge our Credit Card in the amount of \$100.00 covering the fee set forth in 37 CFR 1.20(a). Credit Card Payment Form SB-2038, with a signature from an authorized cardholder, is enclosed.

The errors now sought to be corrected are inadvertent errors the correction of which does not involve new matter or require reexamination.

Transmitted herewith is a proposed Certificate of Correction effecting such amendment. Patentees respectfully solicit the granting of the requested Certificate of Correction.

JAN 16 2007

The Director is authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0439/P439.

Dated: January 10, 2007

Respectfully submitted,

By  #44,198

Thomas J. D'Amico

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Gabriela I. Coman

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JAN 16 2007

**UNITED STATES PATENT AND TRADEMARK OFFICE  
CERTIFICATE OF CORRECTION**

Page 1 of 2

PATENT NO. : 7,142,577  
APPLICATION NO. : 09/855,532  
ISSUE DATE : November 28, 2006  
INVENTORS : Joseph E. Geusic et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Other Publications portion of References Cited, the following publication is added:

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1

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**Should read**

--Berti, M.; Mazzi, G.; Calagnile, L.; Drigo, A.V.; Merli, P.G.; Migliori, A., Composition and structure of Si-Ge layers produced by ion implantation and laser melting, J. Mater. Res., 6(10) Oct. 1991, 2120-2126.--; and

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